

CMPT4401 NPN
CMPT4403 PNP

**SURFACE MOUNT
COMPLEMENTARY
SILICON TRANSISTORS**



SOT-23 CASE



www.centralemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT4401 and CMPT4403 are complementary silicon transistors manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for small signal general purpose amplifier and switching applications.

**MARKING CODES: CMPT4401: C2X
CMPT4403: C2T**

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL	CMPT4401	CMPT4403	UNITS
V_{CBO}	60	40	V
V_{CEO}	40	40	V
V_{EBO}	6.0	5.0	V
I_C	600		mA
P_D	225		mW
T_J, T_{stg}	-65 to +150		$^\circ\text{C}$
Θ_{JA}	556		$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	CMPT4401		CMPT4403		UNITS
		MIN	MAX	MIN	MAX	
I_{CEV}	$V_{CE}=35\text{V}, V_{EB}=0.4\text{V}$	-	0.1	-	0.1	μA
I_{BEV}	$V_{CE}=35\text{V}, V_{EB}=0.4\text{V}$	-	0.1	-	0.1	μA
BV_{CBO}	$I_C=100\mu\text{A}$	60	-	40	-	V
BV_{CEO}	$I_C=1.0\text{mA}$	40	-	40	-	V
BV_{EBO}	$I_E=100\mu\text{A}$	6.0	-	5.0	-	V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	0.40	-	0.40	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	0.75	-	0.75	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	0.75	0.95	0.75	0.95	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	1.2	-	1.3	V
h_{FE}	$V_{CE}=1.0\text{V}, I_C=0.1\text{mA}$	20	-	30	-	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=1.0\text{mA}$	40	-	60	-	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$	80	-	100	-	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=150\text{mA}$	100	300	-	-	
h_{FE}	$V_{CE}=2.0\text{V}, I_C=150\text{mA}$	-	-	100	300	
h_{FE}	$V_{CE}=2.0\text{V}, I_C=500\text{mA}$	40	-	20	-	
f_T	$V_{CE}=10\text{V}, I_C=20\text{mA}, f=100\text{MHz}$	250	-	200	-	MHz
C_{ob}	$V_{CB}=5.0\text{V}, I_E=0, f=1.0\text{MHz}$	-	6.5	-	8.5	pF
C_{ib}	$V_{BE}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$	-	30	-	30	pF

R7 (29-June 2021)

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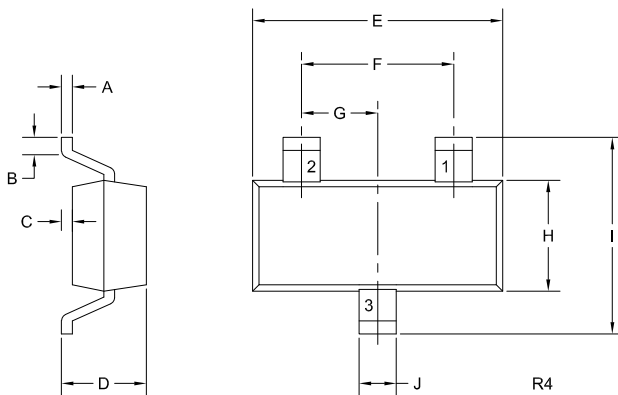
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	CMPT4401		CMPT4403		UNITS
		MIN	MAX	MIN	MAX	
h_{ie}	$V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$	1.0	15	1.5	15	$k\Omega$
h_{re}	$V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$	0.1	8.0	0.1	8.0	$\times 10^{-4}$
h_{fe}	$V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$	40	500	60	500	
h_{oe}	$V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$	1.0	30	1.0	100	μS
t_d	$V_{CC}=30\text{V}$, $V_{BE}=2.0\text{V}$, $I_C=150\text{mA}$, $I_{B1}=15\text{mA}$	-	15	-	15	ns
t_r	$V_{CC}=30\text{V}$, $V_{BE}=2.0\text{V}$, $I_C=150\text{mA}$, $I_{B1}=15\text{mA}$	-	20	-	20	ns
t_s	$V_{CC}=30\text{V}$, $I_C=150\text{mA}$, $I_{B1}=I_{B2}=15\text{mA}$	-	225	-	225	ns
t_f	$V_{CC}=30\text{V}$, $I_C=150\text{mA}$, $I_{B1}=I_{B2}=15\text{mA}$	-	30	-	50	ns

SOT-23 CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.044	0.89	1.12
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.104	2.10	2.64
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R4)

LEAD CODE:

- 1) Base
- 2) Emitter
- 3) Collector

MARKING CODES:

CMPT4401: C2X
CMPT4403: C2T

R7 (29-June 2021)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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